



DONGGUAN NANJING ELECTRONICS LTD.,

SOT-23 Plastic-Encapsulate Transistors

A1015LT1 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 0.2 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

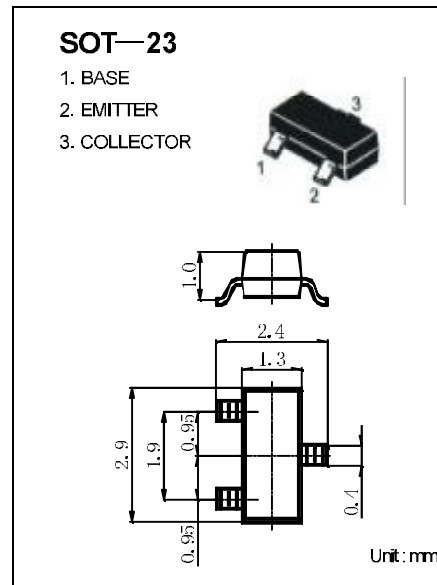
$$I_{CM} : -0.15 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -50 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50 \text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -50 \text{V}, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{V}, I_C = 0$			-0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = -6 \text{V}, I_C = -2 \text{mA}$	130		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$			-1.1	V
Transition frequency	f_T	$V_{CE} = -10 \text{V}, I_C = -1 \text{mA}$ $f = 30 \text{MHz}$	80			MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	L	H
Range	130-200	200-400
MARKING	BA	